10. Operating Conditions

H51010-2.3

Recommended Operating Conditions

Tables 10–1 through 10–4 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 1.8-V HardCopy® APEX™ devices.

Table 10–1. HardCopy APEX Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	2.5	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–0.5	4.6	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	°C
T_{AMB}	Ambient temperature	Under bias	–65	135	°C
T_J	Junction temperature	BGA packages, under bias		135	°C

Table 10–2. HardCopy APEX Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	1.71 (1.71)	1.89 (1.89)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	*(2)*, *(5)*	–0.5	4.1	V
V_O	Output voltage		0	V_{CCIO}	V
T_J	Junction temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time (10% to 90%)			40	ns
t_F	Input fall time (90% to 10%)			40	ns

Table 10–3. HardCopy APEX Device DC Operating Conditions (Part 1 of 2) *Notes (6), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(8)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(8)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(9)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(9)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(9)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(9)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(9)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(9)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(10)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(10)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(10)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(10)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(10)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(10)*			0.7	V
I_I	Input pin leakage current *(11)*	V_I = 4.1 to –0.5 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current *(11)*	V_O = 4.1 to –0.5 V	–10		10	µA

Table 10–3. HardCopy APEX Device DC Operating Conditions (Part 2 of 2) Notes (6), (7), (8)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -7 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -8, -9 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration emulation	V_{CCIO} = 3.0 V *(12)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(12)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(12)*	60		150	kΩ

Table 10–4. HardCopy APEX Device Capacitance Note (13)

Symbol	Parameter	Conditions	Min	Typ	Max
C_{IN}	Input capacitance	V_{IN} = 0 V, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	V_{IN} = 0 V, f = 1.0 MHz		12	pF
C_{OUT}	Output capacitance	V_{OUT} = 0 V, f = 1.0 MHz		8	pF

Notes to Table 10–1 through 10–4:

(1) Refer to the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input is –0.5 V. During transitions, the inputs may undershoot to –0.5 V or overshoot to 4.6 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms, and V_{CC} must rise monotonically.
(5) All pins (including dedicated inputs, clock, I/O, and JTAG pins) may be driven before V_{CCINT} and V_{CCIO} are powered.
(6) Typical values are for T_A = 25° C, V_{CCINT} = 1.8 V, and V_{CCIO} = 1.8 V, 2.5 V, or 3.3 V.
(7) These values are specified under the HardCopy device recommended operating conditions, as shown in Table 10–2 on page 10–1.
(8) Refer to *AN 117: Using Selectable I/O Standards in Altera Devices* for the V_{IH}, V_{IL}, V_{OH}, V_{OL}, and I_I parameters when V_{CCIO} = 1.8 V.
(9) The APEX 20KE input buffers are compatible with 1.8-V, 2.5-V and 3.3-V (LVTTL and LVCMOS) signals. Additionally, the input buffers are 3.3-V PCI compliant. Input buffers also meet specifications for GTL+, CTT, AGP, SSTL-2, SSTL-3, and HSTL.
(10) The I_{OH} parameter refers to high-level TTL, PCI, or CMOS output current.
(11) This value is specified for normal device operation. The value may vary during power-up.
(12) Pin pull-up resistance values will be lower if an external source drives the pin higher than V_{CCIO}.
(13) Capacitance is sample-tested only.

Tables 10–5 through 10–20 list the DC operating specifications for the supported I/O standards. These tables list minimal specifications only; HardCopy devices may exceed these specifications.

Table 10–5. LVTTL I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.8	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	I_{OH} = –12 mA, V_{CCIO} = 3.0 V *(1)*	2.4		V
V_{OL}	Low-level output voltage	I_{OL} = 12 mA, V_{CCIO} = 3.0 V *(2)*		0.4	V

Table 10–6. LVCMOS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Power supply voltage range		3.0	3.6	V
V_{IH}	High-level input voltage		2.0	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.8	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	V_{CCIO} = 3.0 V I_{OH} = –0.1 mA *(1)*	V_{CCIO} – 0.2		V
V_{OL}	Low-level output voltage	V_{CCIO} = 3.0 V I_{OL} = 0.1 mA *(2)*		0.2	V

Table 10–7. 2.5-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		2.375	2.625	V
V_{IH}	High-level input voltage		1.7	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3	0.7	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	I_{OH} = –0.1 mA *(1)*	2.1		V
		I_{OH} = –1 mA *(1)*	2.0		V
		I_{OH} = –2 mA *(1)*	1.7		V
V_{OL}	Low-level output voltage	I_{OL} = 0.1 mA *(2)*		0.2	V
		I_{OL} = 1 mA *(2)*		0.4	V
		I_{OL} = 2 mA *(2)*		0.7	V

Table 10–8. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		1.7	1.9	V
V_{IH}	High-level input voltage		0.65 × V_{CCIO}	V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage			0.35 × V_{CCIO}	V
I_I	Input pin leakage current	V_{IN} = 0 V or 3.3 V	–10	10	µA
V_{OH}	High-level output voltage	I_{OH} = –2 mA *(1)*	V_{CCIO} – 0.45		V
V_{OL}	Low-level output voltage	I_{OL} = 2 mA *(2)*		0.45	V

Table 10–9. 3.3-V PCI Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		0.5 × V_{CCIO}		V_{CCIO} + 0.5	V

Table 10–9. 3.3-V PCI Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{IL}	Low-level input voltage		–0.5		$0.3 \times V_{CCIO}$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	–10		10	µA
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	$0.9 \times V_{CCIO}$			V
V_{OL}	Low-level output voltage	I_{OUT} = 1,500 µA			$0.1 \times V_{CCIO}$	V

Table 10–10. 3.3-V PCI-X Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage		–0.5		$0.35 \times V_{CCIO}$	V
V_{IPU}	Input pull-up voltage		$0.7 \times V_{CCIO}$			V
I_{IL}	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	–10.0		10.0	µA
V_{OH}	High-level output voltage	I_{OUT} = –500 µA	$0.9 \times V_{CCIO}$			V
V_{OL}	Low-level output voltage	I_{OUT} = 1500 µA			$0.1 \times V_{CCIO}$	V
L_{PIN}	Pin Inductance				15.0	nH

Table 10–11. 3.3-V LVDS I/O Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.135	3.3	3.465	V
V_{OD}	Differential output voltage	R_L = 100 Ω	250		450	mV
V_{OD}	Change in VOD between high and low	R_L = 100 Ω			50	mV
V_{OS}	Output offset voltage	R_L = 100 Ω	1.125	1.25	1.375	V

Table 10–11. 3.3-V LVDS I/O Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{OS}	Change in VOS between high and low	R_L = 100 Ω			50	mV
V_{TH}	Differential input threshold	V_{CM} = 1.2 V	–100		100	mV
V_{IN}	Receiver input voltage range		0.0		2.4	V
R_L	Receiver differential input resistor (external to APEX 20K devices)		90	100	110	Ω

Table 10–12. GTL+ I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{TT}	Termination voltage		1.35	1.5	1.65	V
V_{REF}	Reference voltage		0.88	1.0	1.12	V
V_{IH}	High-level input voltage		V_{REF} + 0.1			V
V_{IL}	Low-level input voltage				V_{REF} – 0.1	V
V_{OL}	Low-level output voltage	I_{OL} = 36 mA *(2)*			0.65	V

Table 10–13. SSTL-2 Class I Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V

Table 10–13. SSTL-2 Class I Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{OH}	High-level output voltage	I_{OH} = –7.6 mA *(1)*	V_{TT} + 0.57			V
V_{OL}	Low-level output voltage	I_{OL} = 7.6 mA *(2)*			V_{TT} – 0.57	V

Table 10–14. SSTL-2 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		V_{REF} – 0.04	V_{REF}	V_{REF} + 0.04	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		V_{REF} + 0.18		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.18	V
V_{OH}	High-level output voltage	I_{OH} = –15.2 mA *(1)*	V_{TT} + 0.76			V
V_{OL}	Low-level output voltage	I_{OL} = 15.2 mA *(2)*			V_{TT} – 0.76	V

Table 10–15. SSTL-3 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{TT} + 0.6			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{TT} – 0.6	V

Table 10–16. SSTL-3 Class II Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		1.3	1.5	1.7	V
V_{IH}	High-level input voltage		V_{REF} + 0.2		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.2	V
V_{OH}	High-level output voltage	I_{OH} = –16 mA *(1)*	V_{TT} + 0.8			V
V_{OL}	Low-level output voltage	I_{OL} = 16 mA *(2)*			V_{TT} – 0.8	V

Table 10–17. HSTL Class I I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		1.71	1.8	1.89	V
V_{TT}	Termination voltage		V_{REF} – 0.05	V_{REF}	V_{REF} + 0.05	V
V_{REF}	Reference voltage		0.68	0.75	0.90	V
V_{IH}	High-level input voltage		V_{REF} + 0.1		V_{CCIO} + 0.3	V
V_{IL}	Low-level input voltage		–0.3		V_{REF} – 0.1	V
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{CCIO} – 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			0.4	V

Table 10–18. LVPECL Specifications (Part 1 of 2)

Symbol	Parameter	Minimum	Typical	Maximum	Units
V_{CCIO}	Output Supply Voltage	3.135	3.3	3.465	V
V_{IH}	Low-level input voltage	1,300		1,700	mV
V_{IL}	High-level input voltage	2,100		2,600	mV
V_{OH}	Low-level output voltage	1,450		1,650	mV

Table 10–18. LVPECL Specifications (Part 2 of 2)

Symbol	Parameter	Minimum	Typical	Maximum	Units
V_{OL}	High-level output voltage	2,275		2,420	mV
V_{ID}	Input voltage differential	400	600	950	mV
V_{OD}	Output voltage differential	625	800	950	mV
t_r, t_f	Rise and fall time (20 to 80%)	85		325	ps
t_{DSKEW}	Differential skew			25	ps
t_O	Output load		150		Ω
R_L	Receiver differential input resistor		100		Ω

Table 10–19. 3.3-V AGP I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		$0.39 \times V_{CCIO}$		$0.41 \times V_{CCIO}$	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage				$0.3 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$I_{OUT} = –500\ \mu A$	$0.9 \times V_{CCIO}$		3.6	V
V_{OL}	Low-level output voltage	$I_{OUT} = 1500\ \mu A$			$0.1 \times V_{CCIO}$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	–10		10	µA

Table 10–20. CTT I/O Specifications (Part 1 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{TT}/V_{REF} *(3)*	Termination and reference voltage		1.35	1.5	1.65	V
V_{IH}	High-level input voltage		$V_{REF} + 0.2$			V

Table 10–20. CTT I/O Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{IL}	Low-level input voltage				V_{REF} – 0.2	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	–10		10	µA
V_{OH}	High-level output voltage	I_{OH} = –8 mA *(1)*	V_{REF} + 0.4			V
V_{OL}	Low-level output voltage	I_{OL} = 8 mA *(2)*			V_{REF} – 0.4	V
I_O	Output leakage current (when output is high Z)	$GND \leq V_{OUT} \leq V_{CCIO}$	–10		10	µA

Notes to Tables 10–5 through 10–20:

(1) The I_{OH} parameter refers to high-level output current.

(2) The I_{OL} parameter refers to low-level output current. This parameter applies to open-drain pins as well as output pins.

(3) V_{REF} specifies center point of switching range.

Figure 10–1 shows the output drive characteristics of HardCopy APEX devices.

Figure 10–1. Output Drive Characteristics of HardCopy APEX Devices

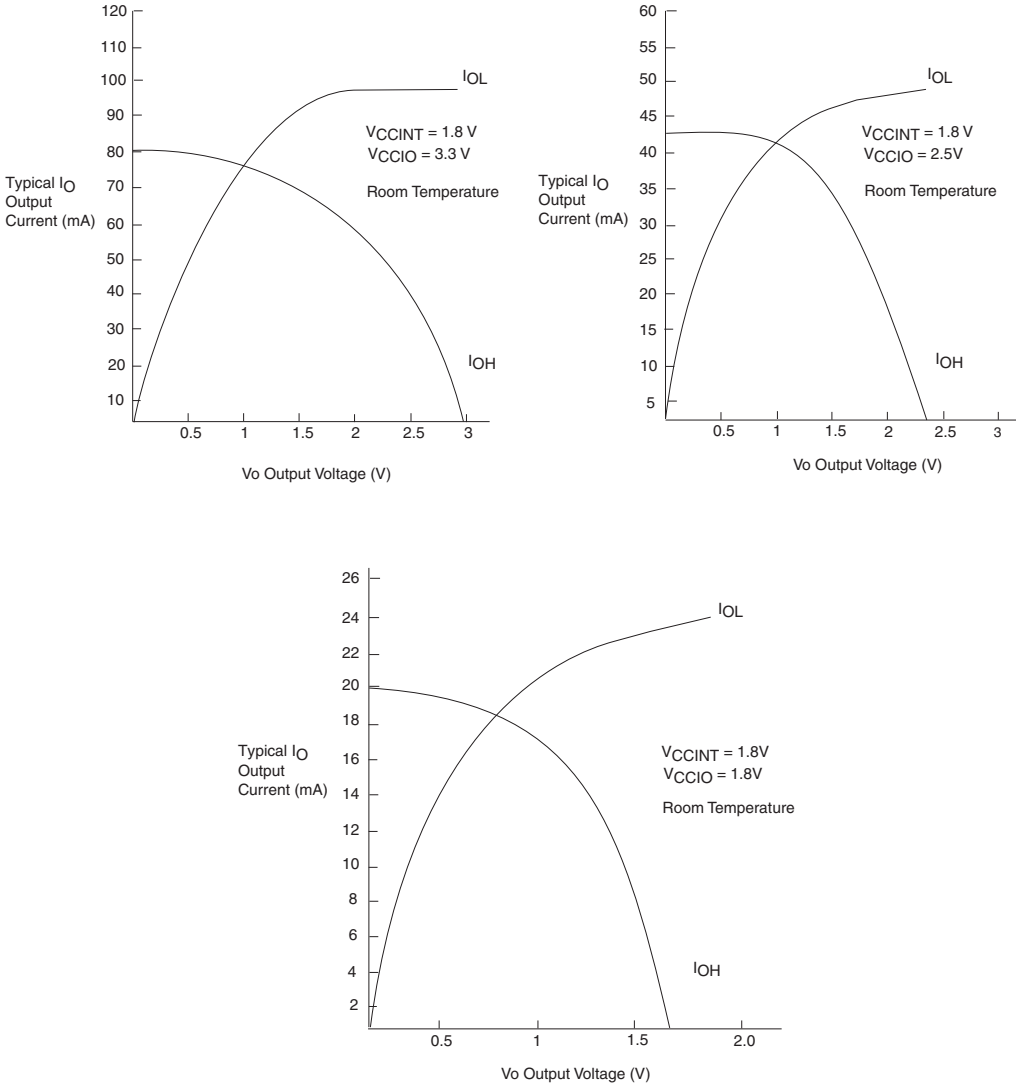
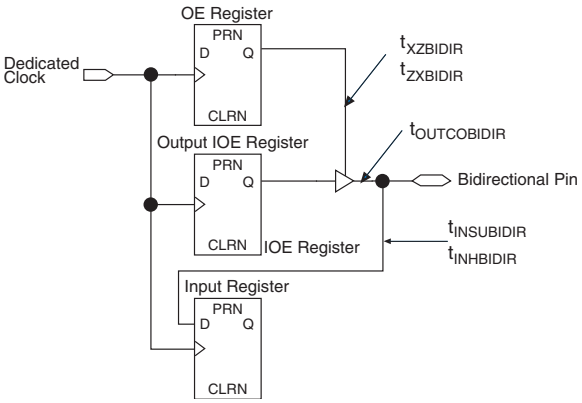


Figure 10–2 shows the timing model for bidirectional I/O pin timing.

Figure 10–2. Synchronous Bidirectional Pin External Timing



Tables 10–21 and 10–22 describe HardCopy APEX device external timing parameters.

Table 10–21. HardCopy APEX Device External Timing Parameters *Note (1)*

Symbol	Clock Parameter	Conditions
t_{INSU}	Setup time with global clock at IOE register	
t_{INH}	Hold time with global clock at IOE register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE output register	C1 = 35 pF
$t_{INSUPLL}$	Setup time with PLL clock at IOE input register	
t_{INHPLL}	Hold time with PLL clock at IOE input register	
$t_{OUTCOPLL}$	Clock-to-output delay with PLL clock at IOE output register	C1 = 35 pF

Table 10–22. HardCopy APEX Device External Bidirectional Timing Parameters (Part 1 of 2) *Note (1)*

Symbol	Parameter	Condition
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 35 pF
$t_{XZBIDIR}$	Synchronous output enable register to output buffer disable delay	C1 = 35 pF

Table 10–22. HardCopy APEX Device External Bidirectional Timing Parameters (Part 2 of 2) Note (1)

Symbol	Parameter	Condition
$t_{ZXBIDIR}$	Synchronous output enable register to output buffer enable delay	C1 = 35 pF
$t_{INSUBIDIRPLL}$	Setup time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{INHBIDIRPLL}$	Hold time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{OUTCOBIDIRPLL}$	Clock-to-output delay for bidirectional pins with PLL clock at IOE register	C1 = 35 pF
$t_{XZBIDIRPLL}$	Synchronous output enable register to output buffer disable delay with PLL	C1 = 35 pF
$t_{ZXBIDIRPLL}$	Synchronous output enable register to output buffer enable delay with PLL	C1 = 35 pF

Note to Tables 10–21 and 10–22:
(1) These timing parameters are sample-tested only.

Tables 10–23 and 10–24 show the external timing parameters for HC20K1500 devices.

Table 10–23. HC20K1500 External Timing Parameters Note (1)

Symbol	Min	Max	Unit
t_{INSU}	2.0		ns
t_{INH}	0.0		ns
t_{OUTCO}	2.0	5.0	ns
$t_{INSUPLL}$	3.3		ns
t_{INHPLL}	0.0		ns
$t_{OUTCOPLL}$	0.5	2.1	ns

Table 10–24. HC20K1500 External Bidirectional Timing Parameters (Part 1 of 2) Note (1)

Symbol	Min	Max	Unit
$t_{INSUBIDIR}$	1.9		ns
$t_{INHBIDIR}$	0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.0	ns
$t_{XZBIDIR}$		7.1	ns
$t_{ZXBIDIR}$		7.1	ns
$t_{INSUBIDIRPLL}$	3.9		ns

Table 10–24. HC20K1500 External Bidirectional Timing Parameters (Part 2 of 2) Note (1)

Symbol	Min	Max	Unit
$t_{INHBIDIRPLL}$	0.0		ns
$t_{OUTCOBIDIRPLL}$	0.5	2.1	ns
$t_{XZBIDIRPLL}$		4.2	ns
$t_{ZXBIDIRPLL}$		4.2	ns

Note to Tables 10–23 and 10–24:
(1) Timing information is preliminary. Final timing information will be available in a future version of this data sheet.

Document Revision History

Table 10–25 shows the revision history for this chapter.

Table 10–25. Document Revision History

Date and Document Version	Changes Made	Summary of Changes
September 2008, v2.3	Updated chapter number and metadata.	—
June 2007, v2.2	Minor text edits.	—
December 2006 v2.1	Updated revision history.	—
March 2006	Formerly chapter 12; no content change.	—
January 2005 v2.0	Update device names and other minor textual changes.	—
June 2003 v1.0	Initial release of *Operating Conditions*, in the HardCopy Device Handbook	—